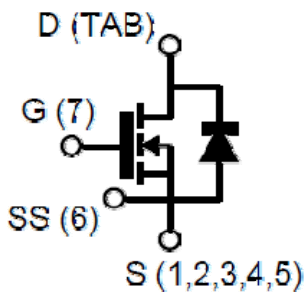
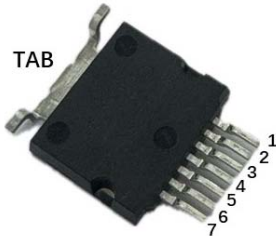


## Silicon Carbide Power MOSFET (N-Channel Enhancement)

$V_{DS}$	1200V
$I_D$ (25°C)	58A
$R_{DS(on)}$	40mΩ



### Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant
- AEC-Q101 qualified

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

- **Package:** T2PAK
- **Terminals:** Tin plated leads
- **Polarity:** As marked

### ■Maximum Ratings ( $T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code				D212040T2GH	
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0\text{ V}$ , $I_D=100\mu\text{A}$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-10/+25	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+20	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	$I_D$	A	58	$V_{GS}=20\text{V}$ , $T_c=25^\circ\text{C}$	
Continuous drain current @ $T_c=110^\circ\text{C}$			38	$V_{GS}=20\text{V}$ , $T_c=110^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	225	Pulse width $t_p$ limited by $T_{j,max}$	
Avalanche energy, Single Pulse	$E_{AS}$	mJ	650	$V_{DD}=75\text{V}$ , $L=30\text{mH}$	
Power Dissipation	$P_{TOT}$	W	278	$T_c=25^\circ\text{C}$ , $T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	$T_j, T_{stg}$	$^\circ\text{C}$	-55 to +175		
Soldering temperature	$T_L$	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	


**■Static Electrical Characteristics** (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	1.5	2.7	4.0	$V_{DS}=V_{GS}$ , $I_D=40mA$	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			$V_{GS}=0$ , $I_D=100\mu A$	
Zero gate voltage drain current	$I_{DSS}$	$\mu A$		<1	50	$V_{DS}=1200V$ , $V_{GS}=0V$	
				10	500	$V_{DS}=1200V$ , $V_{GS}=0V$ , $T_J=175^\circ C$	
Gate source leakage current	$I_{GSS}$	nA			250	$V_{GS}=20V$ , $V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS(on)}$	m $\Omega$		40	52	$V_{GS}=20V$ , $I_D=30A$	
				75		$V_{GS}=20V$ , $I_D=30A$ , $T_J=175^\circ C$	
Transconductance	$g_f$	S		15		$V_{DS}=20V$ , $I_D=30A$	

**■Dynamic Electrical Characteristics** (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	$C_{iss}$	pF		3619		$V_{DS}=800V$ , $V_{GS}=0V$ , $T_J=25^\circ C$ , $f=1MHz$ , $V_{AC}=25mV$	
Output capacitance	$C_{oss}$			145			
Reverse capacitance	$C_{rss}$			18			
Coss stored energy	$E_{oss}$	$\mu J$		59			
Gate source charge	$Q_{gs}$	nC		68		$V_{DS}=800V$ , $V_{GS}=-5/20V$ , $I_D=30A$	
Gate drain charge	$Q_{gd}$			66			
Gate charge	$Q_g$			229			
Internal Gate Resistance	$R_{G(int)}$	$\Omega$		2.0	5.0	$f=1MHz$ , $V_{AC}=25mV$	

**■Switching Characteristics** (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on switching energy	$t_{d(on)}$	ns		11		$V_{DD}=800V$ , $V_{GS}=-5/+20V$ , $I_D=30A$ , $L=100\mu H$ , $R_{G(ext)}=2.7\Omega$	
Turn off switching energy	$t_r$			24.7			
Turn on delay time	$t_{d(off)}$			33.8			
Rise time	$t_r$			14.5			
Turn off delay time	$E_{on}$	$\mu J$		623			
Fall time	$E_{off}$			124			



■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V <sub>SD</sub>	V		3.8		V <sub>GS</sub> =0V, I <sub>SD</sub> =15A	
Continuous diode forward current	I <sub>S</sub>	A		46		V <sub>GS</sub> =0V, Tc=25°C	
Reverse recovery time	trr	nS		65		V <sub>DS</sub> =800V, V <sub>GS</sub> =0V, I <sub>SD</sub> =15A, di/dt=300A/uS	
Reverse recovery charge	Qrr	nC		160			
Peak reverse recovery current	Irrm	A		4.3			

■Thermal Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R <sub>θJ-C</sub>	°C/W	0.54

■Typical Characteristics

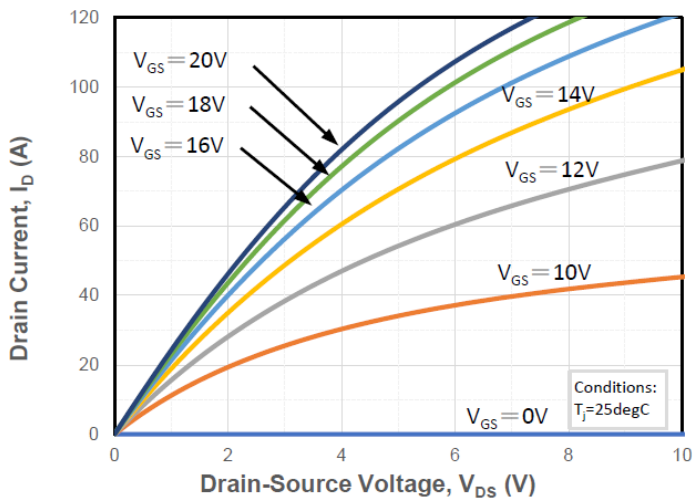


Figure 1. Output Characteristics T<sub>j</sub> = 25°C

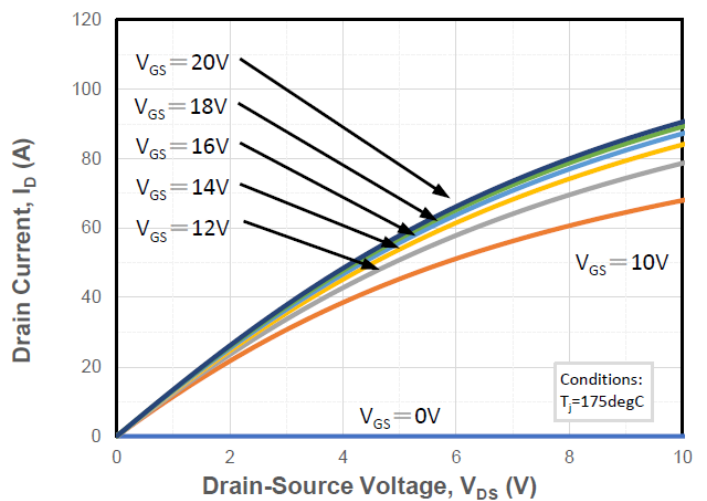


Figure 2. Output Characteristics T<sub>j</sub> = 175°C

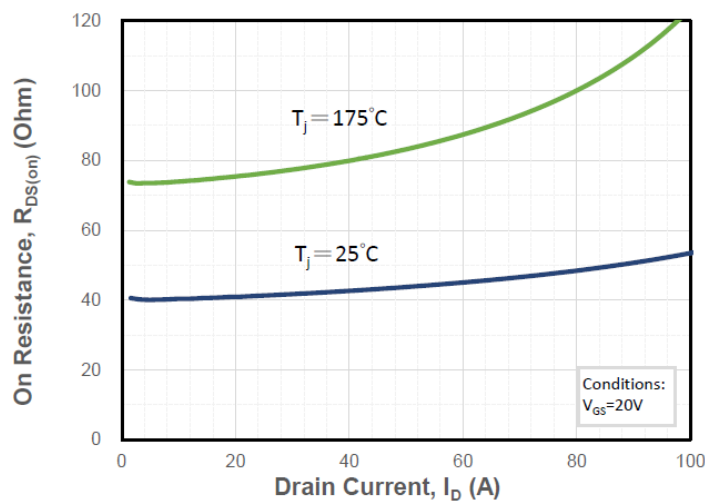


Figure 3. On-resistance vs. drain current

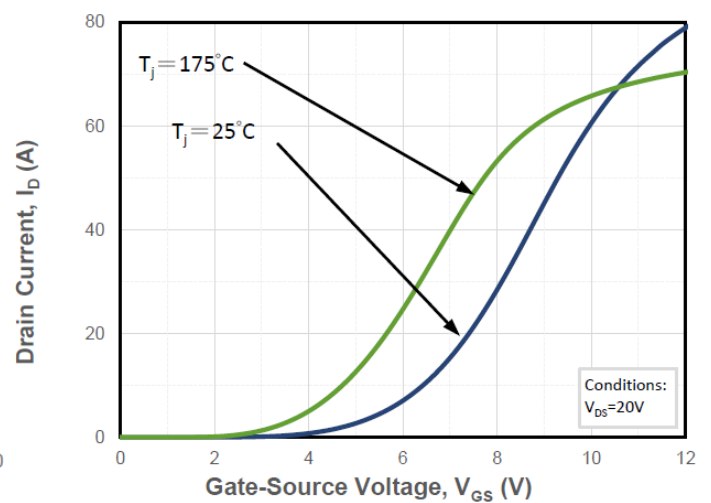


Figure 4. Transfer Characteristics for various T<sub>j</sub>

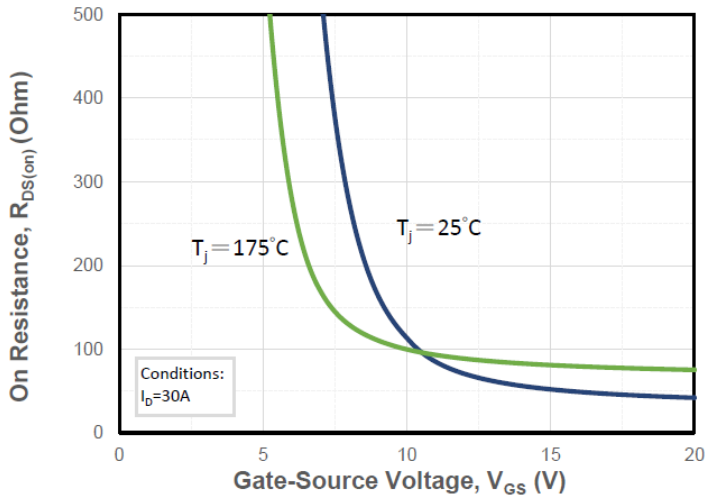


Figure 5. On-resistance vs. gate voltage for various Tj

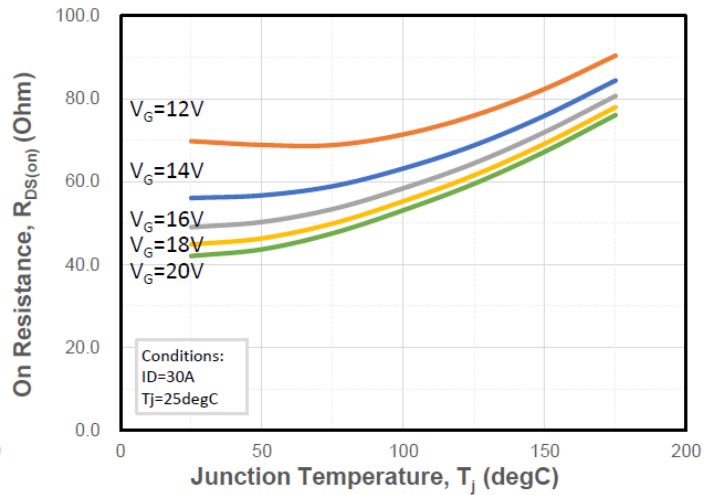


Figure 6. On-resistance vs. Temperature for various Gate voltage

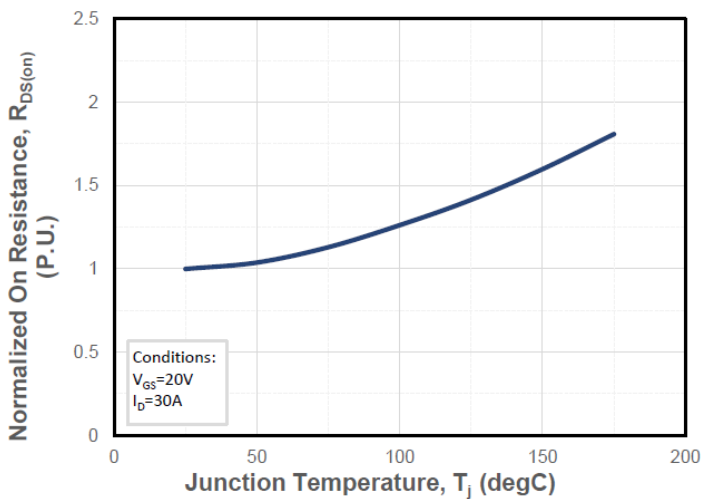


Figure 7. Normalized On-Resistance vs. Temperature

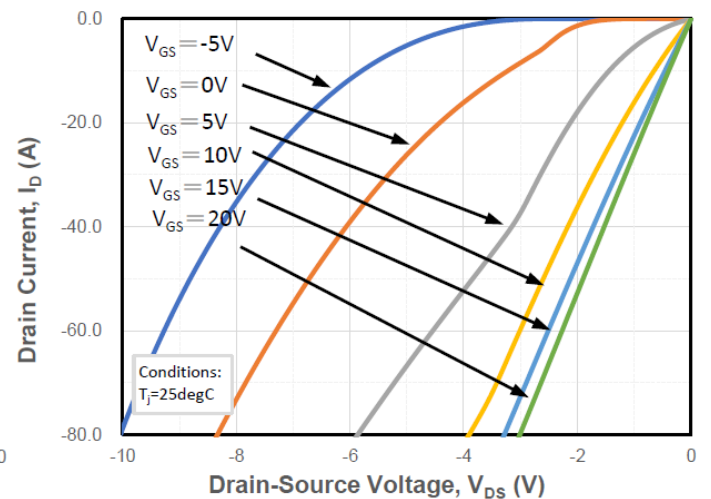


Figure 8. Reverse Output Characteristics at Tj = 25°C

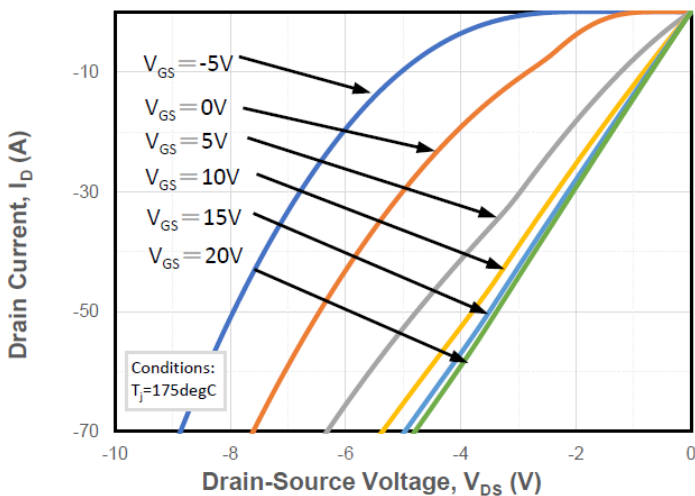


Figure 9. Reverse Output Characteristics at Tj = 175°C

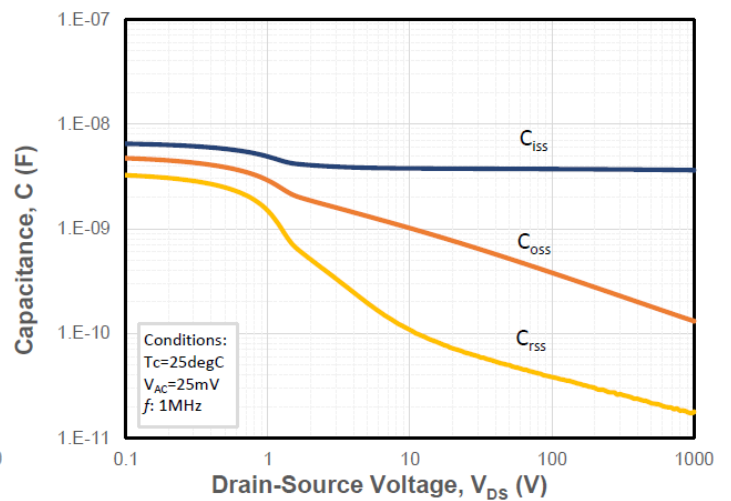


Figure 10. Capacitances vs. Drain to Source Voltage

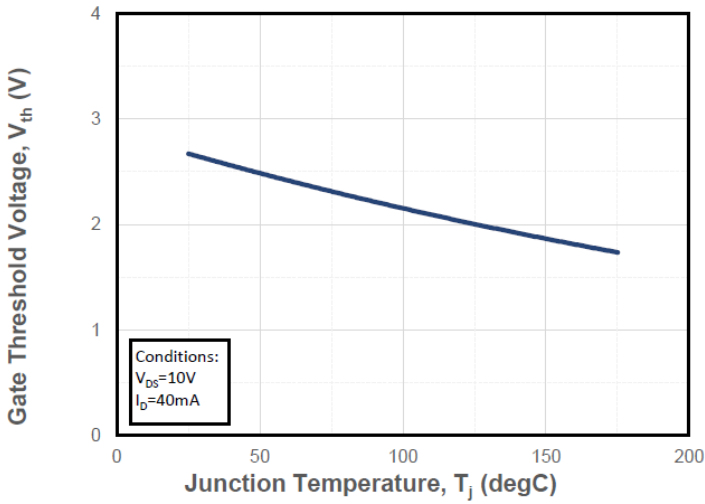


Figure 11. Threshold voltage vs. temperature

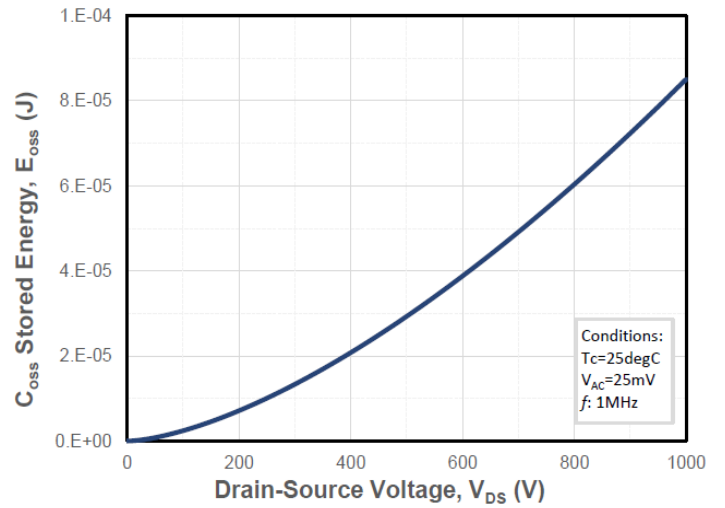


Figure 12. Output Capacitor Stored Energy

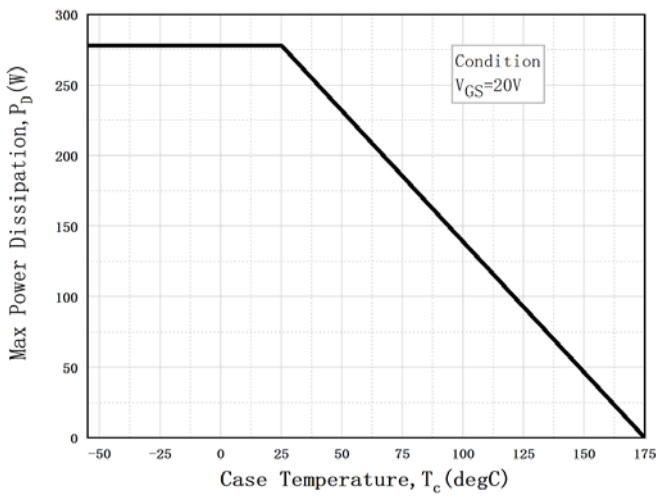


Figure 13. Maximum Power Dissipation Derating vs. Case Temperature

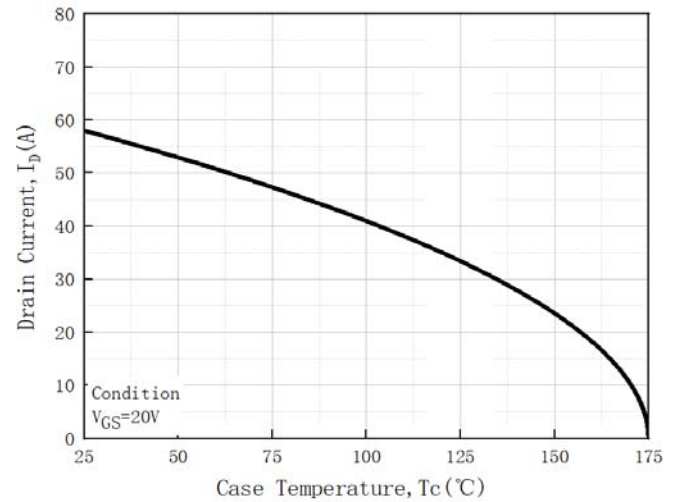


Figure 14. Drain Current Derating vs. Case Temperature

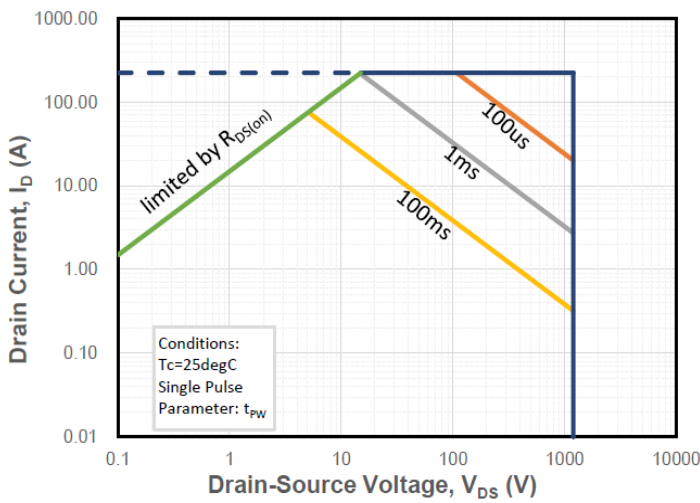


Figure 15. Safe Operating Area

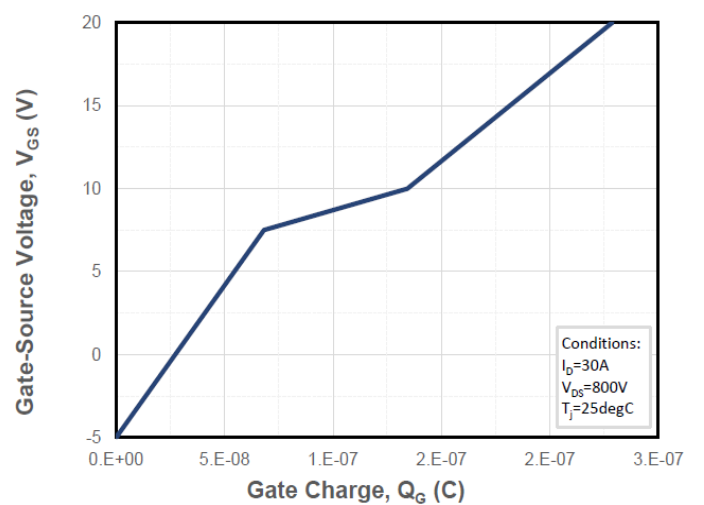


Figure 16. Gate Charge Characteristics

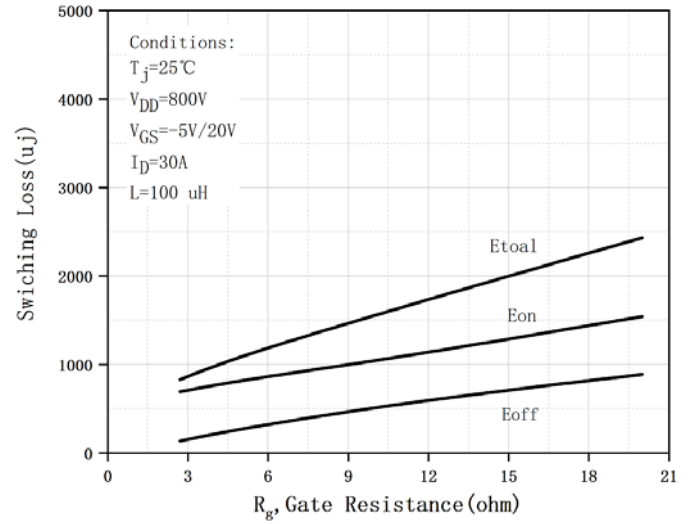
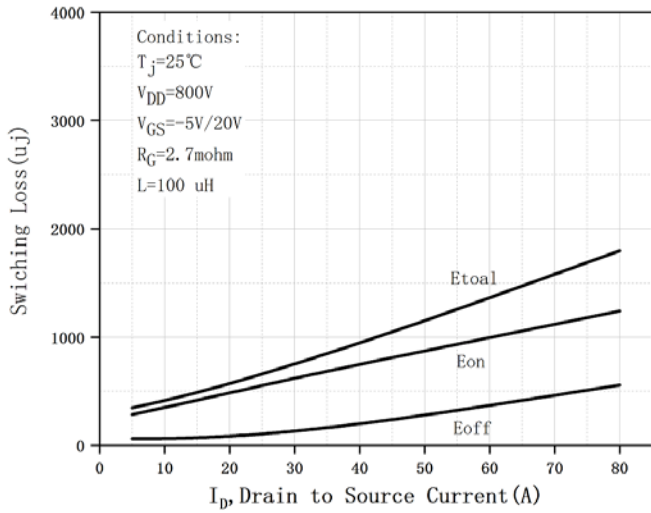


Figure 17. Clamped Inductive Switching Energy vs. Drain Current

Figure 18. Clamped Inductive Switching Energy vs. External Gate Resistor ( $R_{G(ext.)}$ )

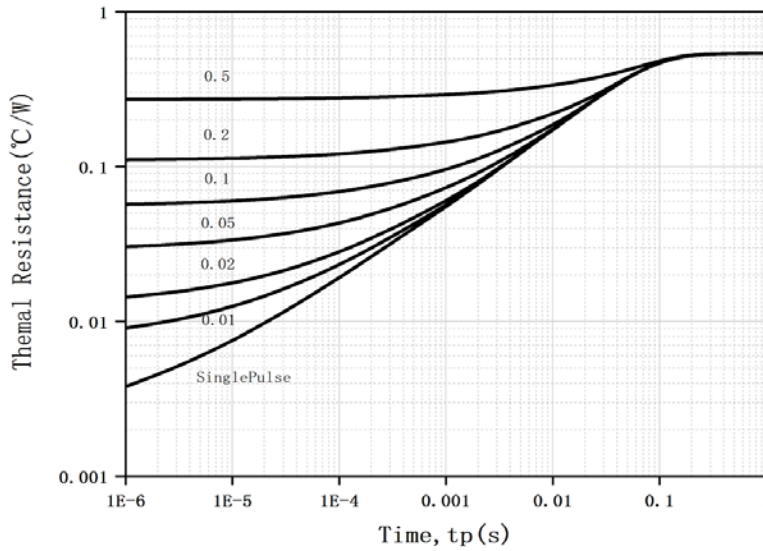


Figure 19. Transient Junction to Case Thermal Impedance

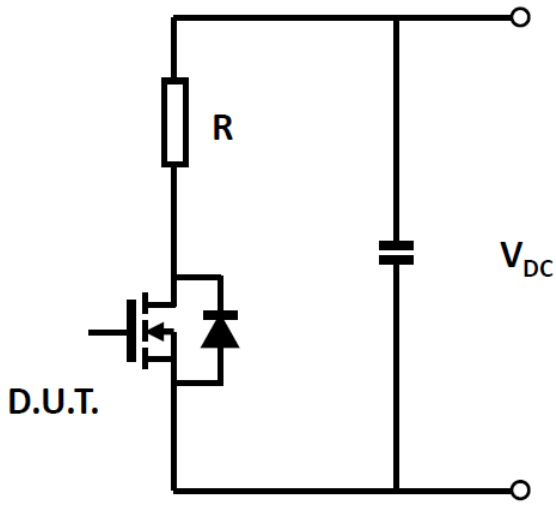


Figure 20. Schematic of Resistive Switching

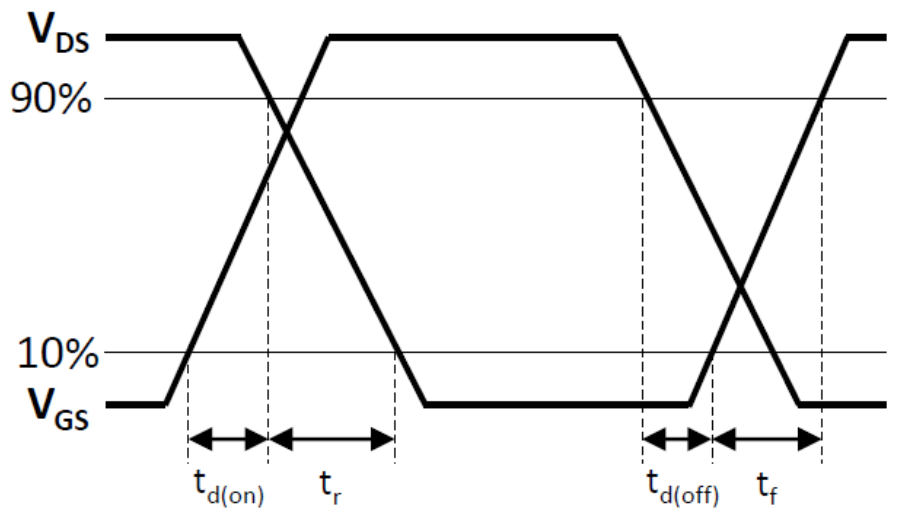
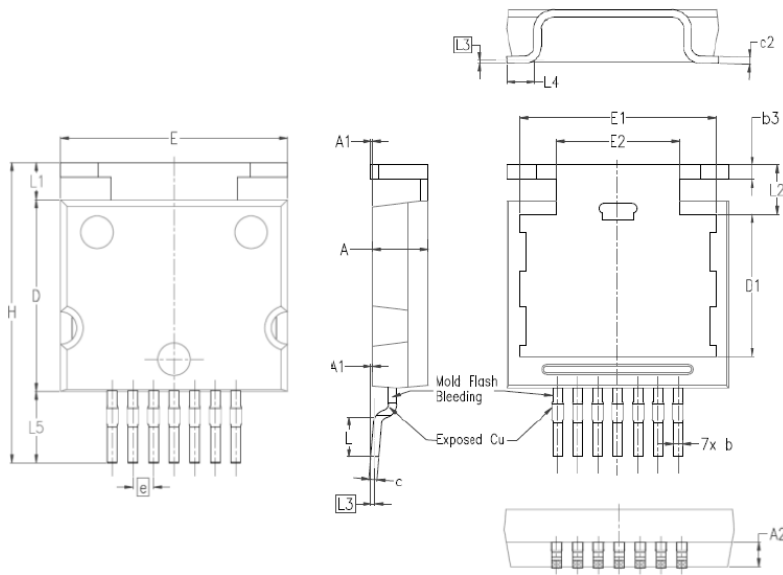


Figure 21. Switching Times Definition

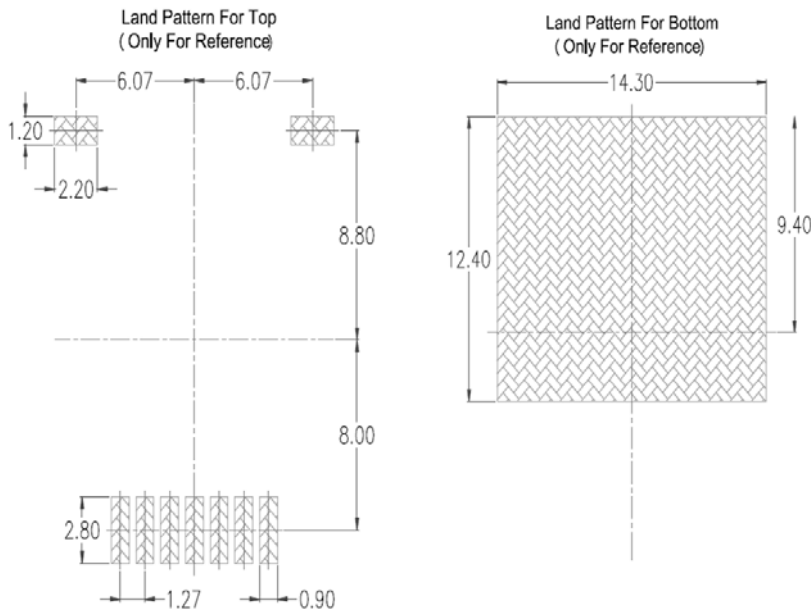


■ Outline Dimensions



Symbol	mm		
	Min.	Typ.	Max.
A	3.30	3.50	3.70
A1	---	0.10	0.25
A2	1.30	1.50	1.70
b	0.50	0.60	0.70
b3	0.80	0.90	1.00
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D	11.70	11.80	11.90
D1	8.80	9.00	9.20
E	13.60	14.00	14.40
E1	12.00	12.40	12.80
E2	7.60	7.80	8.00
e	1.27 BSC		
H	17.70	18.50	19.30
L	1.90	2.50	3.10
L1	2.30 REF		
L2	2.85	3.10	3.35
L3	0.25 BSC		
L4	1.25	1.85	2.45
L5	4.40 REF		

■ Suggested Pad Layout







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